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Burn-in & Test Strategies Workshop

www.bitsworkshop.org

March 6-9, 2016

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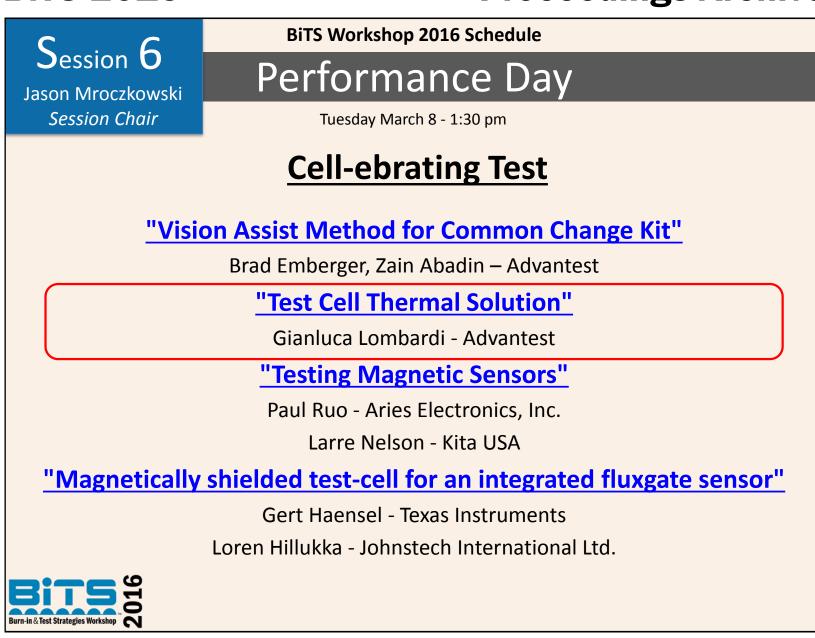
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2

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Cell-ebrating Test - Test Cell - 1 of 2

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Test Cell Thermal Solution

Gianluca Lombardi Advantest



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Cell-ebrating Test - Test Cell - 1 of 2

Overview

- First things first: acronyms!
- Why temperature control?
- Challenges
- Test Cell approach



Test Cell Thermal Solution

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Acronyms!

M4871	Advantest SoC P&P Handler	
93K	Advantest SoC tester	
ATC	Active Thermal Control	
DFT	Design For Testability	
DUT	Device Under Test	
θ _{JC}	Thermal resistance junction/case	
TJ	Junction Temperature	
T _C	Case Temperature	
T _P	Pusher temperature	
T _{HS}	Heat Sink Temperature	



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Why Thermal Control?

- Increasingly temp-sensitive tests
 - VMIN
 - FMAX/speed binning
 - PMIC trimming
 - IDDQ
- Deviations from desired temperature set point lead to incorrect measurements, wrong binning, resulting in either yield loss or RMAs



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Passive/Active Thermal Control

Passive

 The control system maintains the same heat sink temperature at all times

Active

 The control system changes the heat sink temperature in response to temperature variations, to more quickly supply/sink heat to/from the DUT and restore the desired temperature



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Why Active Thermal Control?

- Performance
 - Faster response to temperature variations, everything else being equal
- Correlation
 - Empirical temperature control solutions tend to lead to inconsistent yields from production site to production site



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Thermal Stack

Temperature control quality is the result of all the following contributors

- ATC heat sink
- Package
- Socket
- Handler change kit
- Loadboard



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Continuity vs Thermal Contact

Factors limiting temperature control quality w/Continuity already established

- High thermal resistance between ATC heat sink and package
 - Limited or missing gimbaling
- Package --more on this in the next slide



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Package Challenges

- Junction/case thermal resistance, θ_{JC}
- Top side roughness/markings
 - Roughness = air gaps= higher θ_{JC}
- Planarity
 - Thin packages warping/flattening over T_J
- Contamination



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DUT Challenges

- Temperature feedback availability
 - Thermal diode: always
 - Temp sensors: generally after initialization and ATPG
 - Need additional DFT/resources



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Test Cell Challenges

- Socket/loadboard/DUT/tester can quickly get damaged by thermal runaways
 - Must detect early signs of failure, wherever it may come from
 - Even more so with high power applications, 100W and above



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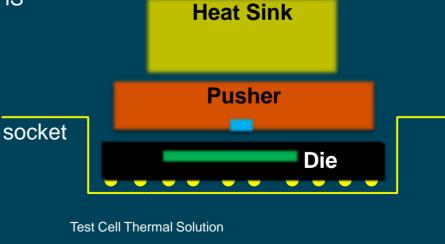
11

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Where to Sense DUT Temperature

- DUT thermal diode (T₁) - One in the whole chip, always available DUT embedded temp sensors - Multiple available generally after init/ATPG - Temperature gradients can be quantified • Heat Sink, T_{HS} **Heat Sink** Pusher, T_{P} ullet
 - Case, T_C



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12

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ATC Challenges (I)

- ATC response time within milliseconds range
 Limited by heat transfer time constants through stack
- Very fast DUT T_J rise transients may come and go before the they get detected and corrected by best-in-class ATC

- Slow heat propagation through thermal stack

• ATC can only do so much, if the thermal stack is highly thermally resistive

– Slow to detect, slow to respond to $\Delta T/\Delta t$



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ATC Challenges (II)

- T_{HS} is M4871 default T measurement source
- T_{HS} may NOT follow T_J very closely
 - with just 10W power being dissipated, $T_{\rm J}$ can raise by 10-12C, while $T_{\rm HS}$ hardly moves by 1-2C,

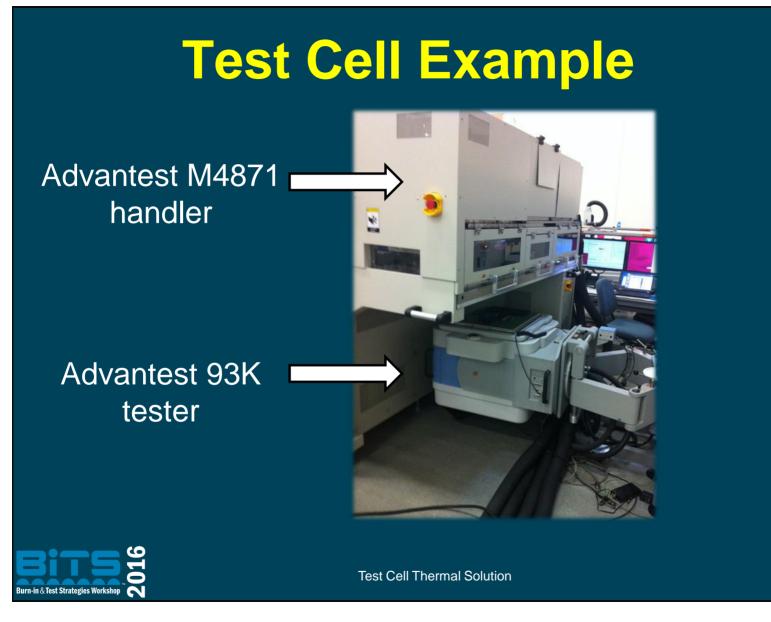


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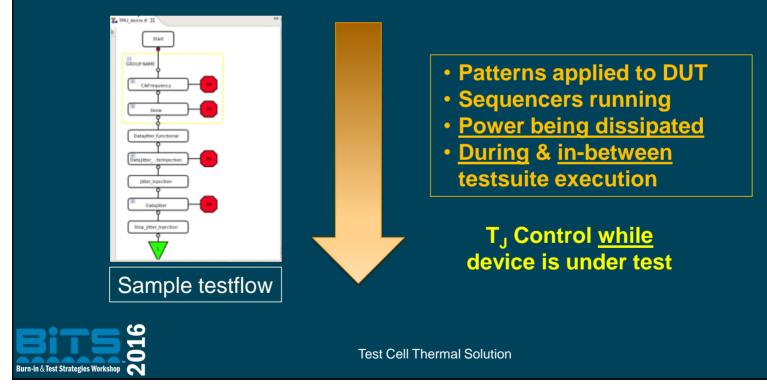
15

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Real-Time Junction Control (T_J)

ATC CONTINUOSLY...

- Measures junction temperature T_J and detects over/under shoots
- Reacts to ΔT_J driven by <u>ALL DUT power domains</u>



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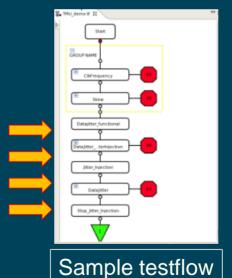
16

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Supported T_J Feedback Types

93K test program controls temperature feedback signal used by M4871

- T_J ANA (diff/SE)
- PWM
- I2C



Feedback mode can be changed testsuite by testsuite

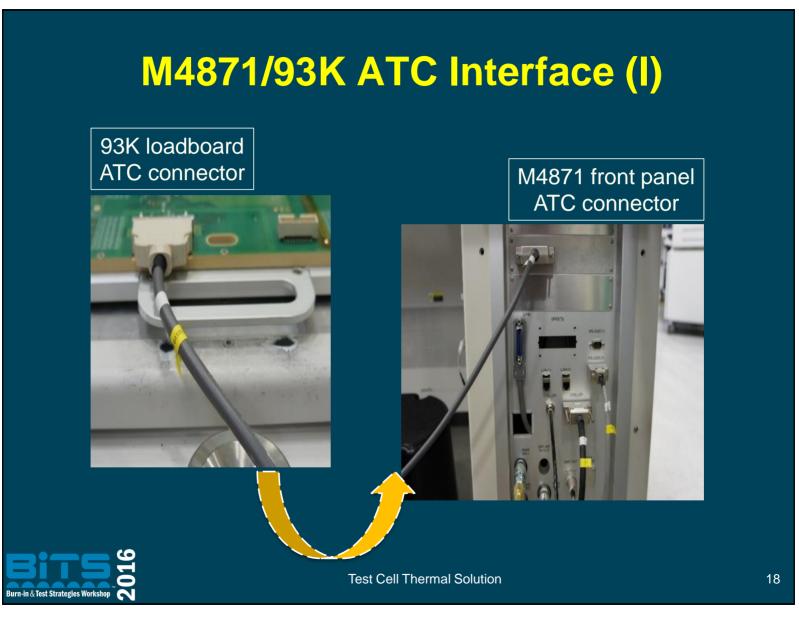


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M4871/93K ATC Interface (II)

Signal	Direction
ANA_TEMP+	Driven by DUT
ANA_TEMP-	Driven by DUT
I2C_DTA	Driven by DUT
I2C_CLK	Driven by DUT
PWM	Driven by DUT



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M4871/93K ATC Interface (III)

Signal	Direction
PROFILE_PRETRIGGER	Driven by 93K
T-CASE_B	Driven by 93K
T-PWM_B	Driven by 93K
M4871_OK_B	Driven by M4871
UHC4_SAFETY_LINE_B	Driven by M4871
CABLE_OK_B	Monitored by 93K



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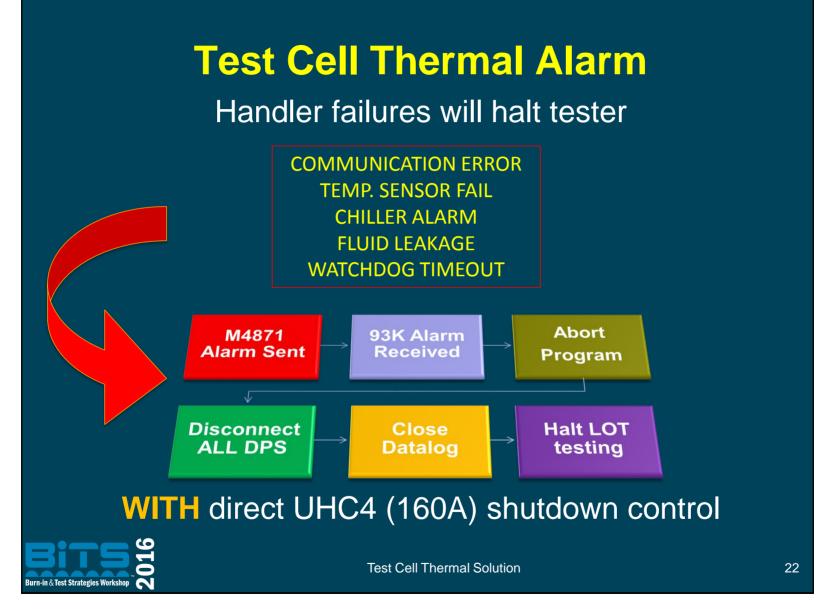


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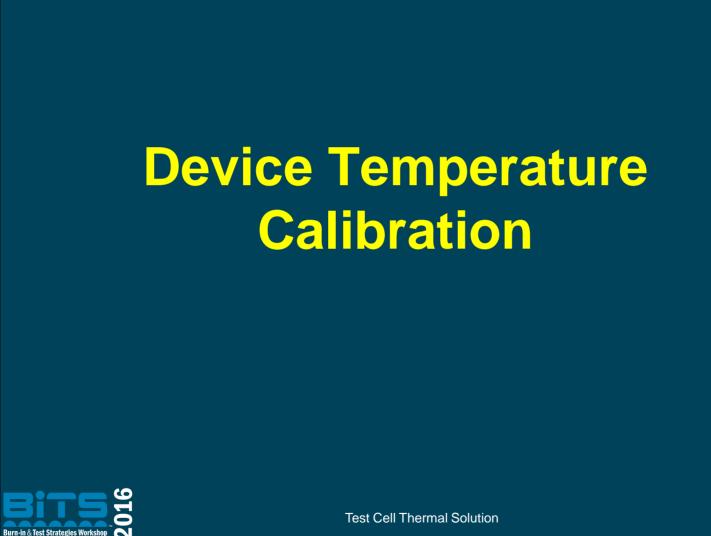
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DUT T/V Calibration (I)

Concept

- Accurate T_J measurement required only during calibration
 - Provided by temperature monitor IC or DUT, once per insertion
- When DUT is at set point (e.g. $T_J = 85C$), thermal diode voltage $\overline{V_{BE}}$ is measured and ATC calibrated

 $\overline{V_{BE}}$: thermal diode voltage measured when DUT @ set point



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DUT T/V Calibration (II)

Concept (cont.)

- After calibration, $V_{BE}(t)$ is monitored by M4871
 - Biasing current supplied by loadboard circuitry or tester channel
- $V_{BE}(t)$ is now the ATC feedback signal, not $T_J(t)$

ATC will minimize $\Delta V_{BE} = \{V_{BE}(t) - \overline{V_{BE}}\}$



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DUT T/V Calibration (III)

Advantages

- Measuring is faster than calculating $T_J(t)$
- NO add'l voltage/temp conversion required after T/V calibration
- Immune to silicon process and ESR
 - Relies on accurate thermal diode ideality factor



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26

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Profiling & Pre-Triggering



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27

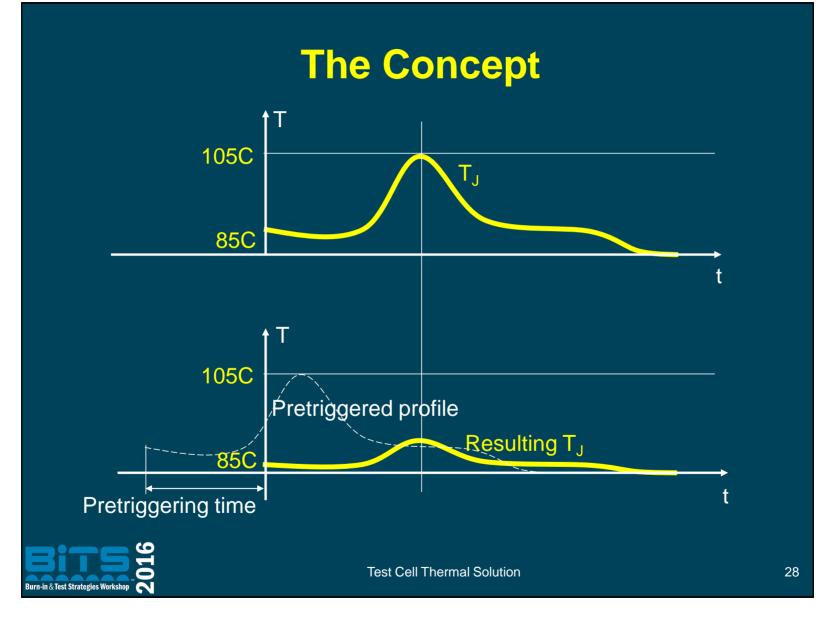
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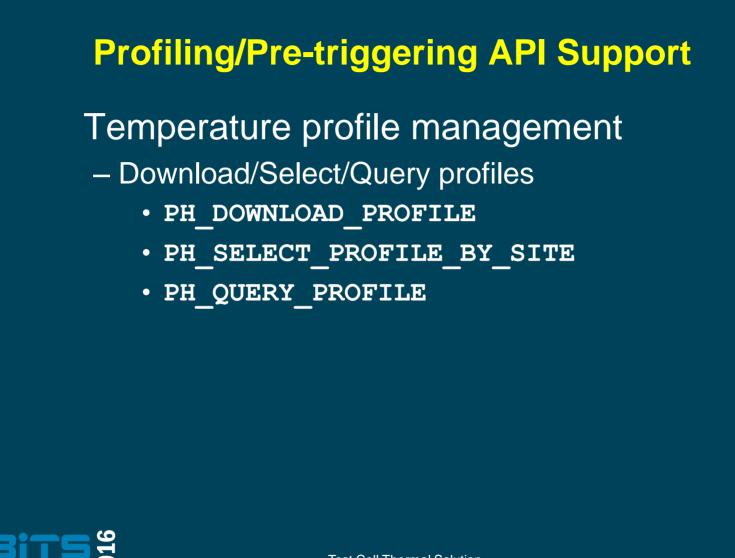
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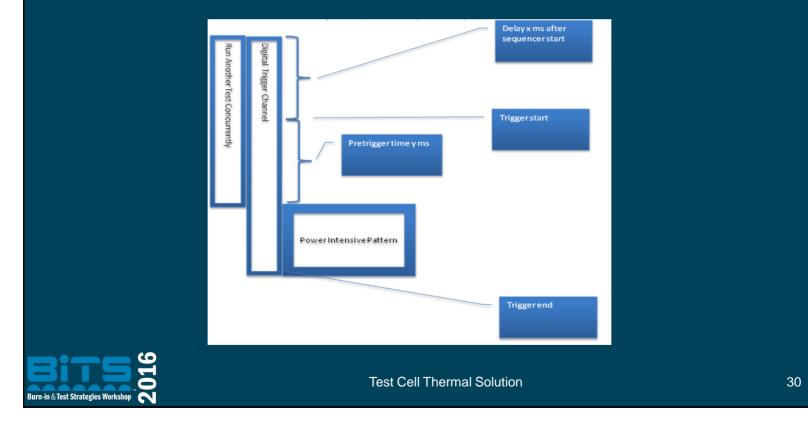
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Profiling/Pre-triggering TML Support

Zero-overhead \rightarrow hides pre-triggering time behind low power pattern



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